Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	3.7	Α
Static characte	Static characteristics						,
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	54	72	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV90ENE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV90ENE	%GH

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.7	Α
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	3	Α
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	1.9	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	12	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	460	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
			[1]	-	1.1	W
		T _{sp} = 25 °C		-	4.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode		'			
I _S	source current	T _{amb} = 25 °C	[1]		1	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

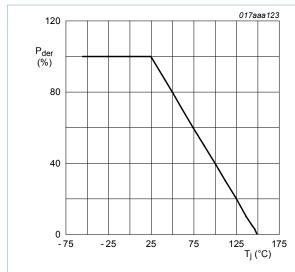


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

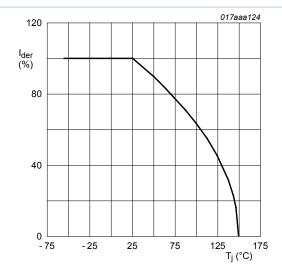


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

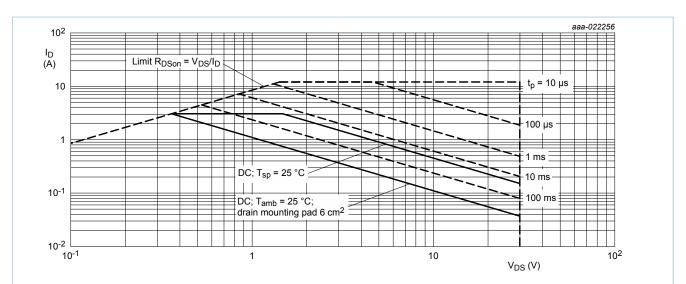


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

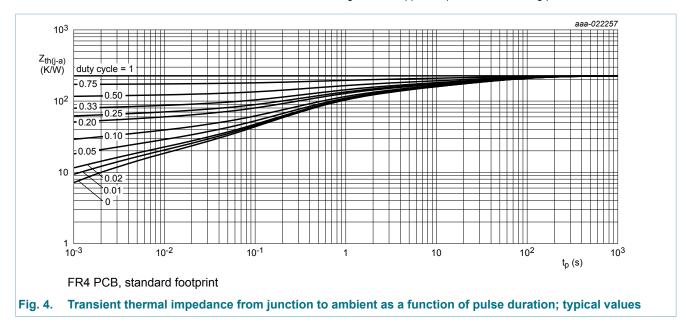
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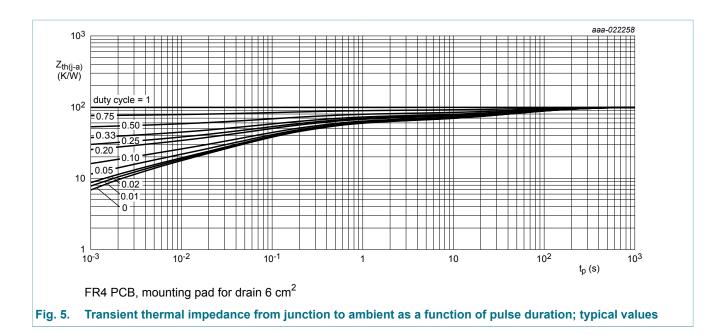
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	227	270	K/W
		[2]	-	99	115	K/W	
	ambient	t ≤ 5 s	<u>[2]</u>	-	66	78	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	20	28	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².





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10. Characteristics

Table 7. Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
racteristics					
drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.5	2.5	V
drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
	V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μA
drain-source on-state	V_{GS} = 10 V; I_D = 3 A; T_j = 25 °C	-	54	72	mΩ
resistance	V _{GS} = 10 V; I _D = 3 A; T _j = 150 °C	-	88	118	mΩ
	$V_{GS} = 4.5 \text{ V}; I_D = 2.6 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	70	100	mΩ
forward transconductance	V_{DS} = 10 V; I_{D} = 3 A; T_{j} = 25 °C	-	9	-	S
gate resistance	f = 1 MHz	-	11.5	-	Ω
haracteristics			'	'	,
total gate charge	V_{DS} = 15 V; I_{D} = 3 A; V_{GS} = 10 V;	-	3.6	5.5	nC
gate-source charge	T _j = 25 °C	-	0.4	-	nC
gate-drain charge		-	0.7	-	nC
input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	160	-	pF
output capacitance	T _j = 25 °C	-	33	-	pF
reverse transfer capacitance		-	26	-	pF
turn-on delay time	V _{DS} = 15 V; I _D = 3 A; V _{GS} = 10 V;	-	6	-	ns
rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
turn-off delay time		-	11	-	ns
fall time		-	4	-	ns
ain diode	1		-1	1	
source-drain voltage	I _S = 1 A; V _{GS} = 0 V; T _i = 25 °C	_	0.8	1.2	V
	drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current drain-source on-state resistance forward transconductance gate resistance haracteristics total gate charge gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time ain diode	racteristics drain-source breakdown voltage gate-source threshold voltage drain leakage current $V_{DS} = 30 \text{ V}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ gate leakage current $V_{DS} = 30 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$ $V_{GS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$ $V_{GS} = 4.5 \text{ V}; I_D = 2.6 \text{ A}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$ $V_{DS} = 15 \text{ V}; I_D = 3 \text{ A}; V_{GS} = 10 \text{ V}; I_D = 3 \text{ A}; I_$	racteristics drain-source breakdown voltage $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ 30 gate-source threshold voltage $I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ 1 drain leakage current gate leakage current $V_{DS} = 30 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - drain-source on-state resistance $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - forward transconductance $V_{DS} = 10 \ V; \ I_D = 3 \ A; \ T_j = 25 \ ^{\circ}C$ - - forward transconductance $V_{DS} = 15 \ V; \ I_D = 3 \ A; \ V_{GS} = 10 \ V;$ - - gate resistance $f = 1 \ MHz$ - - haracteristics - - - total gate charge $V_{DS} = 15 \ V; \ I_D = 3 \ A; \ V_{GS} = 0 \ V;$ <td>tracteristics drain-source breakdown voltage $I_D = 250 \mu A; V_{GS} = 0 V; T_J = 25 ^{\circ}C$ 30 - gate-source threshold voltage $I_D = 250 \mu A; V_{DS} = V_{GS}; T_J = 25 ^{\circ}C$ 1 1.5 drain leakage current voltage $V_{DS} = 30 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - gate leakage current voltage $V_{GS} = 20 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - $V_{GS} = 10 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - - $V_{GS} = 10 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - drain-source on-state resistance $V_{GS} = 10 V; I_D = 3 A; T_J = 25 ^{\circ}C$ - - drain-source on-state resistance $V_{GS} = 10 V; I_D = 3 A; T_J = 25 ^{\circ}C$ - - drain-source on-state resistance $V_{GS} = 10 V; I_D = 3 A; T_J = 25 ^{\circ}C$ - - drain-source on-state resistance $V_{GS} = 10 V; I_D = 3 A; T_J = 25 ^{\circ}C$ - - drain-source on-state resistance $V_{DS} = 10 V; I_D = 3 A; V_{GS} = 10 V;$ - 9 total gate charge gate resistance $V_{DS} = 15 V; I_D = 3 A;$</td> <td>drain-source breakdown voltage I_D = 250 μA; V_{GS} = 0 V; T_J = 25 °C 30 - - gate-source threshold voltage I_D = 250 μA; V_{DS}=V_{GS}; T_J = 25 °C 1 1.5 2.5 drain leakage current voltage V_{DS} = 30 V; V_{DS} = 0 V; T_J = 25 °C - - 1 gate leakage current voltage V_{DS} = 30 V; V_{DS} = 0 V; T_J = 25 °C - - 10 V_{GS} = 220 V; V_{DS} = 0 V; T_J = 25 °C - - - 10 V_{GS} = 10 V; V_{DS} = 0 V; T_J = 25 °C - <td< td=""></td<></td>	tracteristics drain-source breakdown voltage $I_D = 250 \mu A; V_{GS} = 0 V; T_J = 25 ^{\circ}C$ 30 - gate-source threshold voltage $I_D = 250 \mu A; V_{DS} = V_{GS}; T_J = 25 ^{\circ}C$ 1 1.5 drain leakage current voltage $V_{DS} = 30 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - gate leakage current voltage $V_{GS} = 20 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - $V_{GS} = 10 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - - $V_{GS} = 10 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - drain-source on-state resistance $V_{GS} = 10 V; I_D = 3 A; T_J = 25 ^{\circ}C$ - - drain-source on-state resistance $V_{GS} = 10 V; I_D = 3 A; T_J = 25 ^{\circ}C$ - - drain-source on-state resistance $V_{GS} = 10 V; I_D = 3 A; T_J = 25 ^{\circ}C$ - - drain-source on-state resistance $V_{GS} = 10 V; I_D = 3 A; T_J = 25 ^{\circ}C$ - - drain-source on-state resistance $V_{DS} = 10 V; I_D = 3 A; V_{GS} = 10 V;$ - 9 total gate charge gate resistance $V_{DS} = 15 V; I_D = 3 A;$	drain-source breakdown voltage I _D = 250 μA; V _{GS} = 0 V; T _J = 25 °C 30 - - gate-source threshold voltage I _D = 250 μA; V _{DS} =V _{GS} ; T _J = 25 °C 1 1.5 2.5 drain leakage current voltage V _{DS} = 30 V; V _{DS} = 0 V; T _J = 25 °C - - 1 gate leakage current voltage V _{DS} = 30 V; V _{DS} = 0 V; T _J = 25 °C - - 10 V _{GS} = 220 V; V _{DS} = 0 V; T _J = 25 °C - - - 10 V _{GS} = 10 V; V _{DS} = 0 V; T _J = 25 °C - <td< td=""></td<>

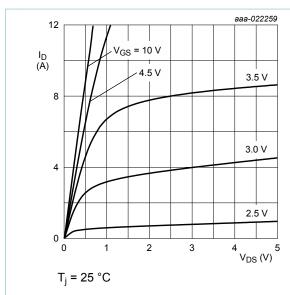


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

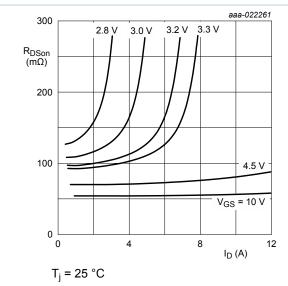


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

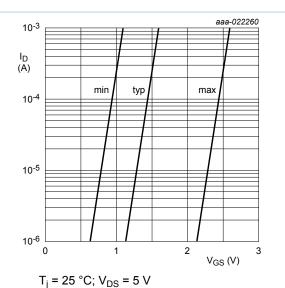


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

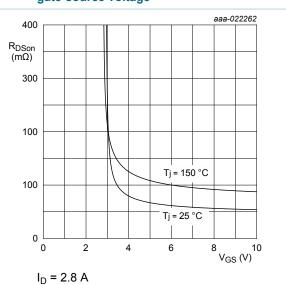


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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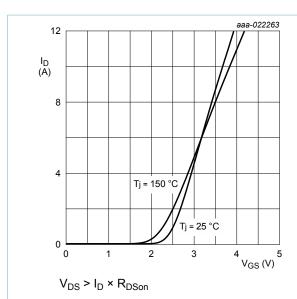


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

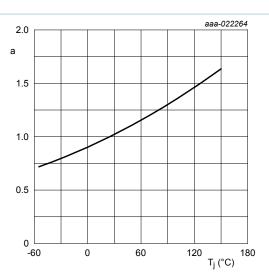


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

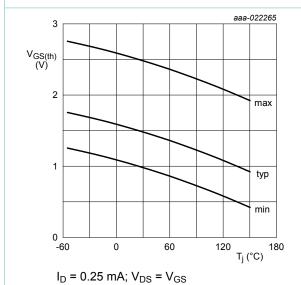
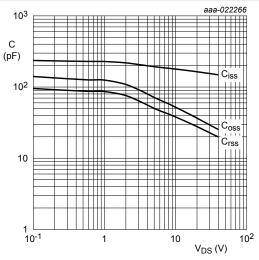


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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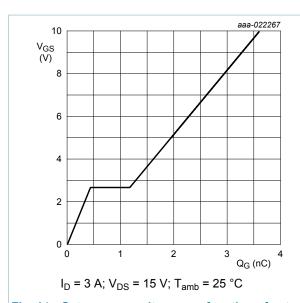


Fig. 14. Gate-source voltage as a function of gate charge; typical values

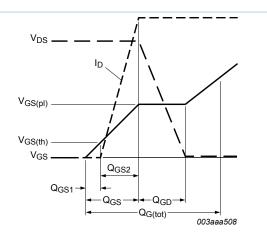


Fig. 15. MOSFET transistor: Gate charge waveform definitions

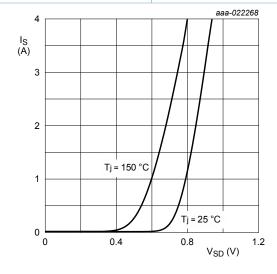
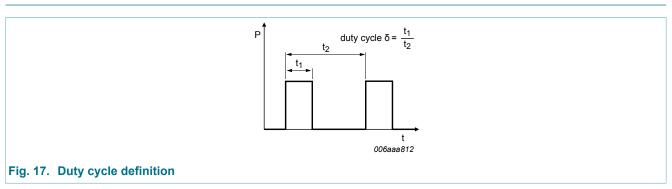


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$

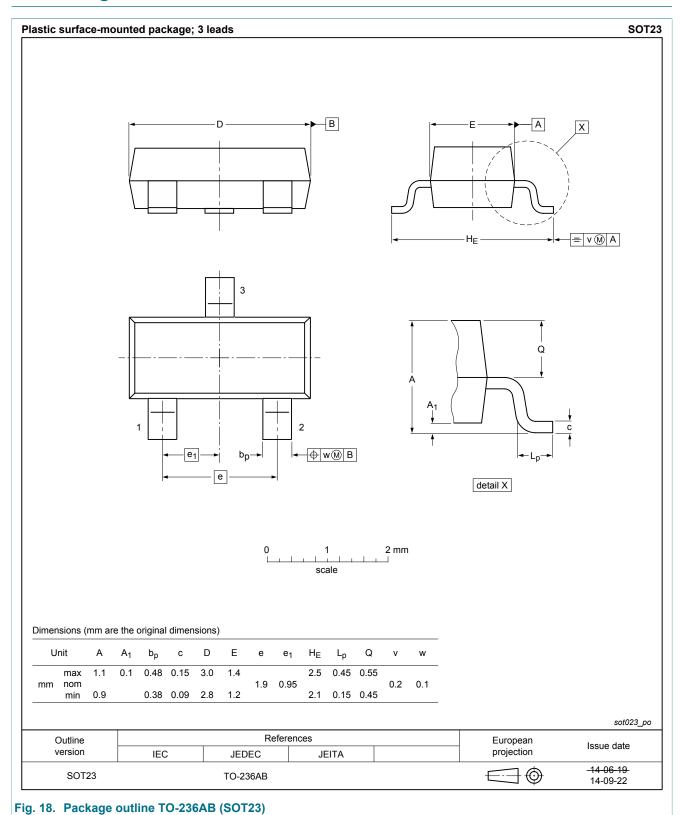


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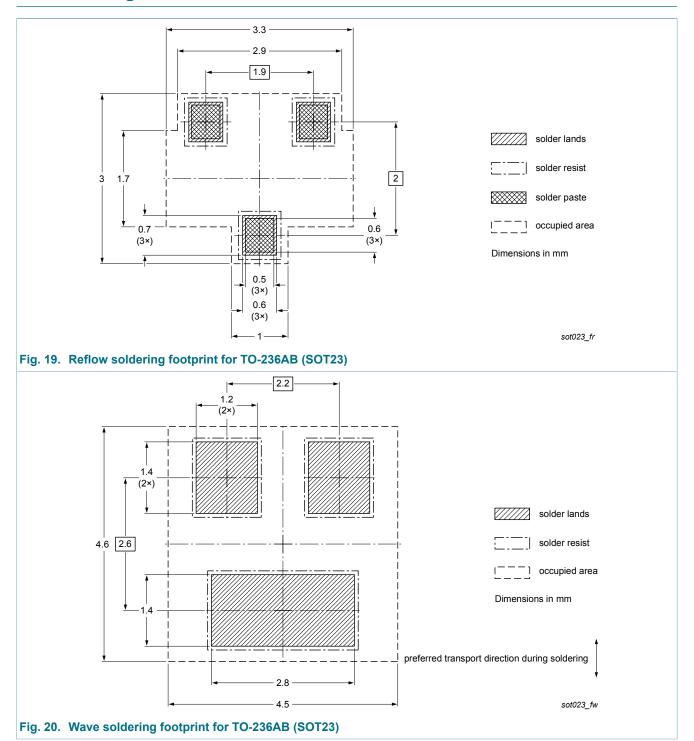
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV90ENE v.1	20160420	Product data sheet	-	-

30 V, N-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

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